



N-channel Enhancement Mode Mosfet

CX3075B

DESCRIPTION

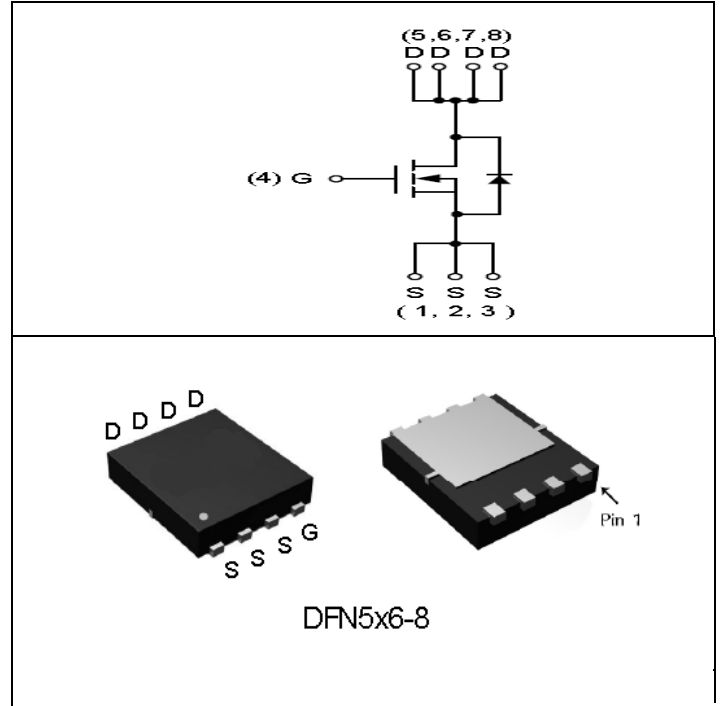
The CX3075B uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- $R_{DS(ON)} < 8m\Omega$ @ $V_{GS}=4.5V$
 $R_{DS(ON)} < 5m\Omega$ @ $V_{GS}=10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^\circ C$	I_D	60	A
	$T_C=100^\circ C$		38	
Pulsed Drain Current ^A		I_{DM}	120	A
Total Power Dissipation	$T_C=25^\circ C$	P_D	35	W
	$T_C=100^\circ C$		15	W
Single Pulse Avalanche Energy ^B		E_{AS}	29	mJ
Thermal Resistance Junction-to-Case ^C		$R_{\theta JC}$	3.4	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$